Correction to: Au²⁺-Implanted Regions in Silicon Visualized Using a Modulated Free-Carrier Absorption Method

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The original version of the article unfortunately contained errors in Abstract and Fig. 6.

In Abstract, the first sentence ‘Silicon samples were implanted with Au²⁺ ions of energy 100 keV and doses of 10¹⁴ cm⁻²’ should read ‘Silicon samples were implanted with Au²⁺ ions of energy 200 keV and doses of 10¹⁴ cm⁻²’.

In page 6, the sentence ‘Using the SRIM computer program, the thickness of the implanted layer was found to be $d = 800 \text{ Å}$ (Fig. 6)’ should read ‘Using the SRIM computer program, the thickness of the implanted layer was found to be $d = 1440 \text{ Å}$ (Fig. 6)’. Revised version of Fig. 6 is given below.

The original article can be found online at <https://doi.org/10.1007/s10765-017-2246-2>.

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Fig. 6 Spatial distribution of Au^{2+} ions in silicon computed in the SRIM program

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